

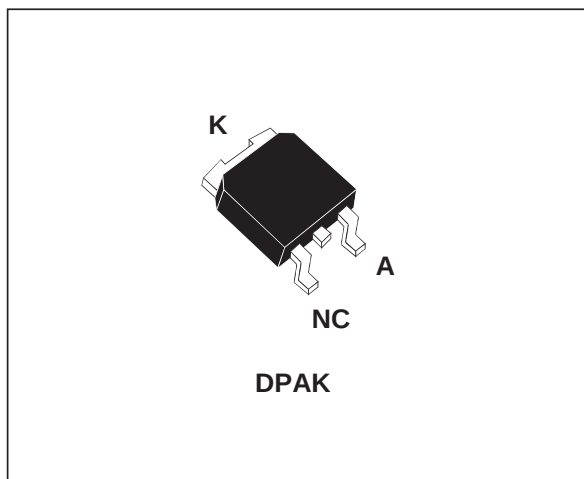
LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	8 A
V_{RRM}	30 V
T_j (max)	150 °C
V_F (max)	0.40 V

FEATURES AND BENEFITS

- LOW COST DEVICE WITH LOW DROP FORWARD VOLTAGE FOR LESS POWER DISSIPATION AND REDUCED HEATSINK
- OPTIMIZED CONDUCTION/REVERSE LOSSES TRADE-OFF WHICH LEADS TO THE HIGHEST YIELD IN THE APPLICATIONS
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

Single Schottky rectifier suited to Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in DPAK, this device is especially intended for use as a Rectifier at the secondary of 3.3V SMPS or DC/DC units.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		30	V
$I_{F(RMS)}$	RMS forward current		7	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ\text{C} \quad \delta = 0.5$	8	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	75	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ $F = 1\text{kHz}$ square	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100\mu\text{s}$ square	2	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1\mu\text{s}$ $T_j = 25^\circ\text{C}$		W
T_{stg}	Storage temperature range		- 65 to + 150	°C
T_j	Maximum junction temperature		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j - a)}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions	Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$		1	mA
		$T_j = 100^\circ\text{C}$		15	40	
V_F *	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$		0.49	V
		$T_j = 125^\circ\text{C}$		0.35	0.4	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$		0.63	
		$T_j = 125^\circ\text{C}$		0.48	0.57	

Pulse test : * $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.23 \times I_{F(AV)} + 0.021 I_{F(RMS)}^2$$

Fig. 1: Average forward power dissipation versus average forward current.

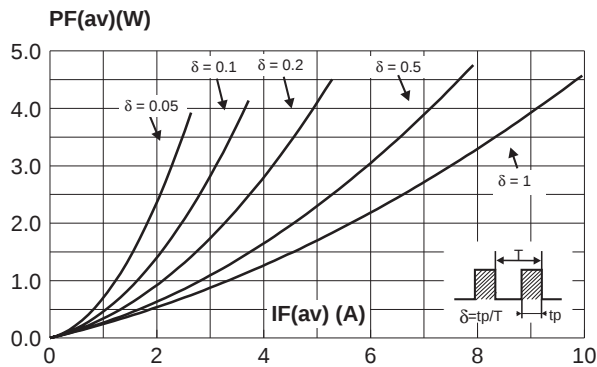


Fig. 3: Normalized avalanche power derating versus pulse duration.

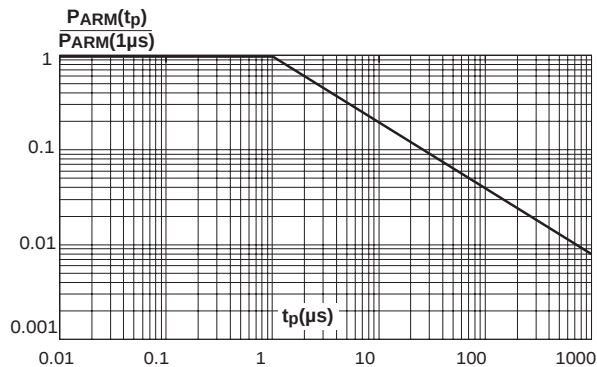


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$).

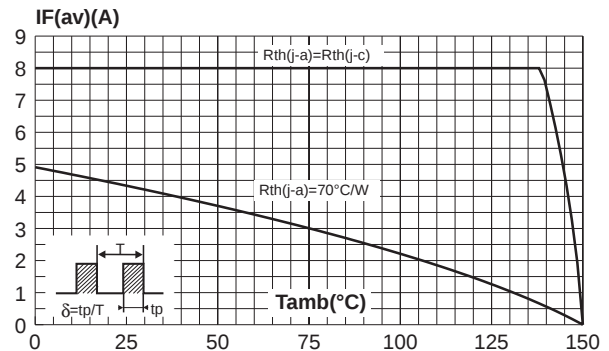


Fig. 4: Normalized avalanche power derating versus junction temperature.

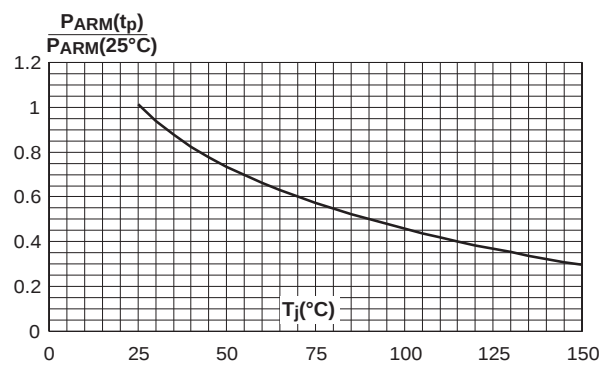


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

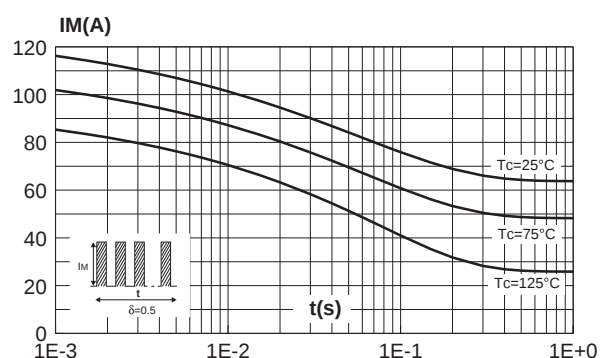


Fig. 6: Relative variation of thermal impedance junction to ambient versus pulse duration.

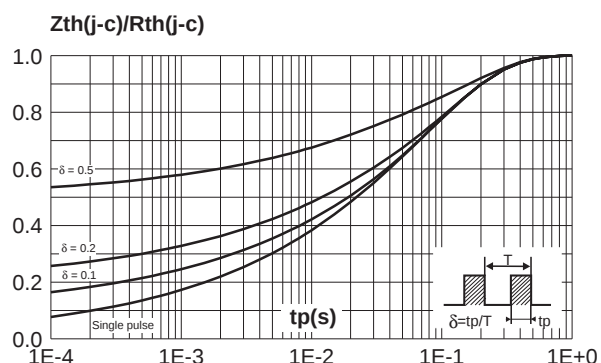


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

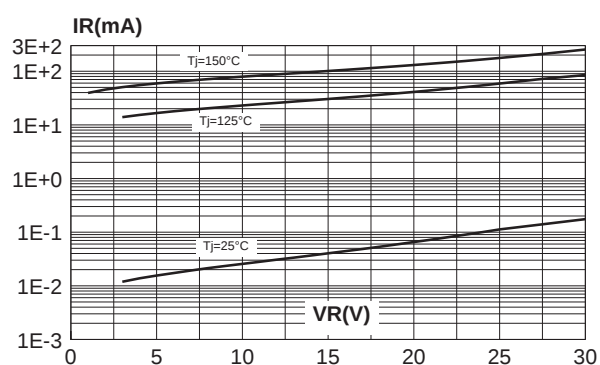


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

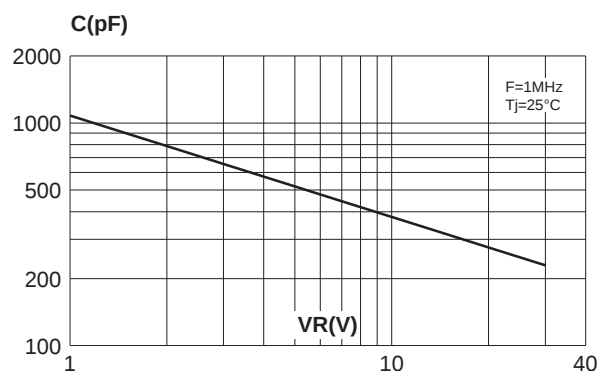
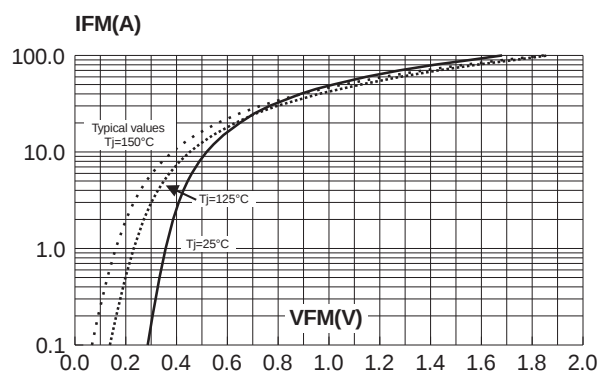


Fig. 9: Forward voltage drop versus forward current (maximum values).



STPS8L30B

PACKAGE MECHANICAL DATA DPAK

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max	Min.	Max.
A	2.20	2.40	0.086	0.094
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
B	0.64	0.90	0.025	0.035
B2	5.20	5.40	0.204	0.212
C	0.45	0.60	0.017	0.023
C2	0.48	0.60	0.018	0.023
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.251	0.259
G	4.40	4.60	0.173	0.181
H	9.35	10.10	0.368	0.397
L2	0.80 typ.		0.031 typ.	
L4	0.60	1.00	0.023	0.039
V2	0°	8°	0°	8°

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS8L30B	ST LS30	DPAK	0.30g	75	Tube

- EPOXY MEETS UL94,V0

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany
Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore
Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>